

# BDV65B (NPN), BDV64B (PNP)

## Complementary Silicon Plastic Power Darlington

... for use as output devices in complementary general purpose amplifier applications.

### Features

- High DC Current Gain – HFE = 1000 (min) @ 5 A<sub>dc</sub>
- Monolithic Construction with Built-in Base Emitter Shunt Resistors
- These are Pb-Free Devices\*

### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current – Continuous – Peak	I <sub>C</sub>	10 20	A <sub>dc</sub>
Base Current	I <sub>B</sub>	0.5	A <sub>dc</sub>
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	125 1.0	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.0	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

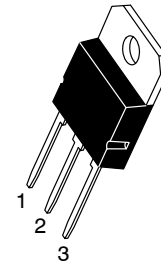
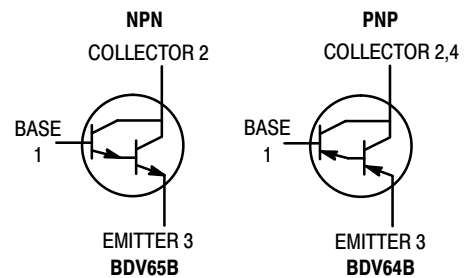
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



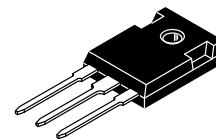
ON Semiconductor®

<http://onsemi.com>

## 10 AMPERE DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS 60-80-100-120 VOLTS, 125 WATTS



SOT-93  
(TO-218)  
CASE 340D



TO-247  
CASE 340L  
STYLE 3

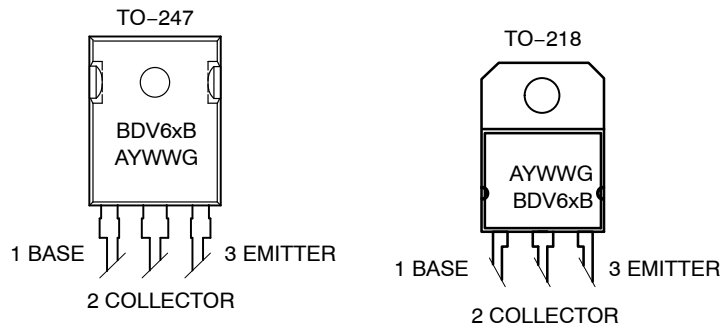
**NOTE:** Effective June 2012 this device will be available only in the TO-247 package. Reference FPCN# 16827.

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# BDV65B (NPN), BDV64B (PNP)

## MARKING DIAGRAMS



BDV6xB = Device Code  
 x = 4 or 5  
 A = Assembly Location  
 Y = Year  
 WW = Work Week  
 G = Pb-Free Package

## ORDERING INFORMATION

Device Order Number	Package Type	Shipping
BDV65BG	TO-218 (Pb-Free)	30 Units / Rail
BDV64BG	TO-218 (Pb-Free)	30 Units / Rail
BDV65BG	TO-247 (Pb-Free)	30 Units / Rail
BDV64BG	TO-247 (Pb-Free)	30 Units / Rail

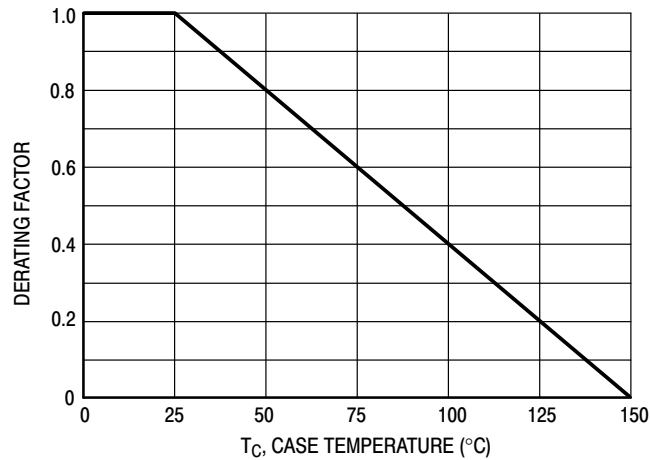


Figure 1. Power Derating

## BDV65B (NPN), BDV64B (PNP)

### ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

#### OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage (1) ( $I_C = 30 \text{ mAdc}$ , $I_B = 0$ )	$V_{CEO(sus)}$	100	–	Vdc
Collector Cutoff Current ( $V_{CE} = 50 \text{ Vdc}$ , $I_B = 0$ )	$I_{CEO}$	–	1.0	mAdc
Collector Cutoff Current ( $V_{CB} = 100 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	–	0.4	mAdc
Collector Cutoff Current ( $V_{CB} = 50 \text{ Vdc}$ , $I_E = 0$ , $T_C = 150^\circ\text{C}$ )	$I_{CBO}$	–	2.0	mAdc
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	5.0	mAdc

#### ON CHARACTERISTICS

DC Current Gain ( $I_C = 5.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ )	$h_{FE}$	1000	–	–
Collector–Emitter Saturation Voltage ( $I_C = 5.0 \text{ Adc}$ , $I_B = 0.02 \text{ Adc}$ )	$V_{CE(sat)}$	–	2.0	Vdc
Base–Emitter Saturation Voltage ( $I_C = 5.0 \text{ Adc}$ , $V_{CE} = 4.0 \text{ Vdc}$ )	$V_{BE(on)}$	–	2.5	Vdc

# BDV65B (NPN), BDV64B (PNP)

NPN

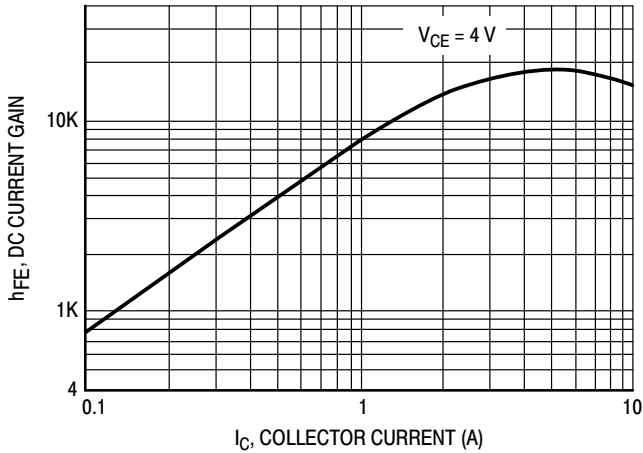


Figure 2. DC Current Gain

PNP

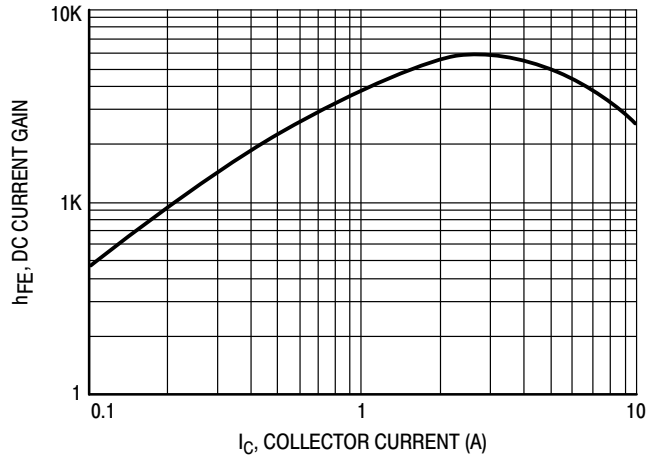


Figure 3. DC Current Gain

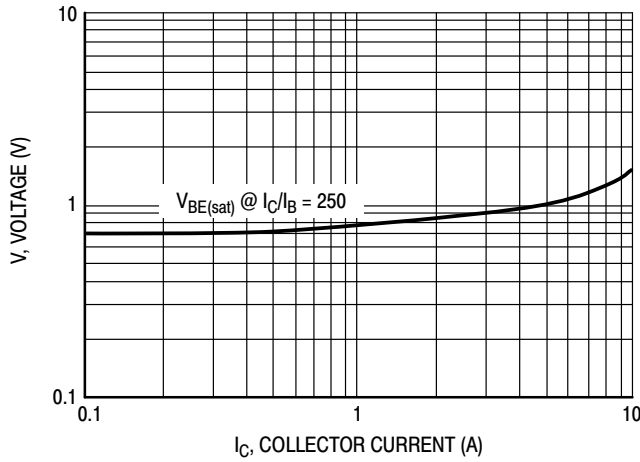


Figure 4. "On" Voltages

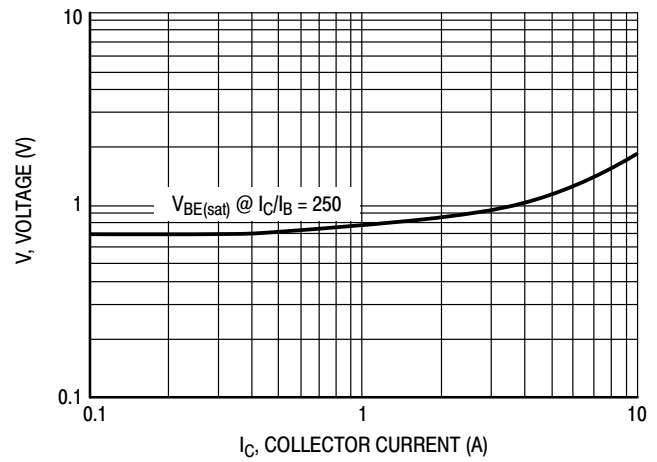


Figure 5. "On" Voltages

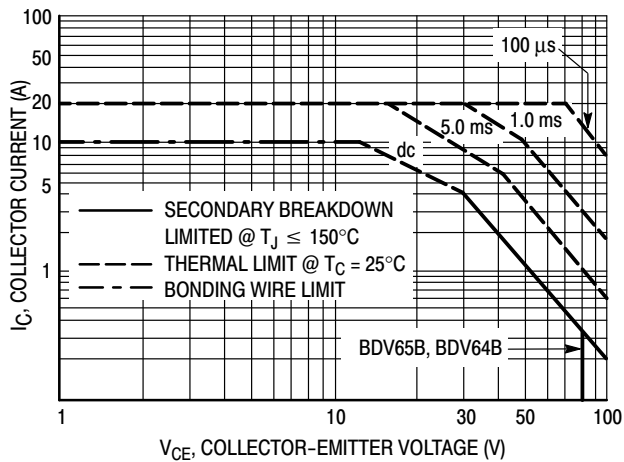


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ,  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 7. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

# BDV65B (NPN), BDV64B (PNP)

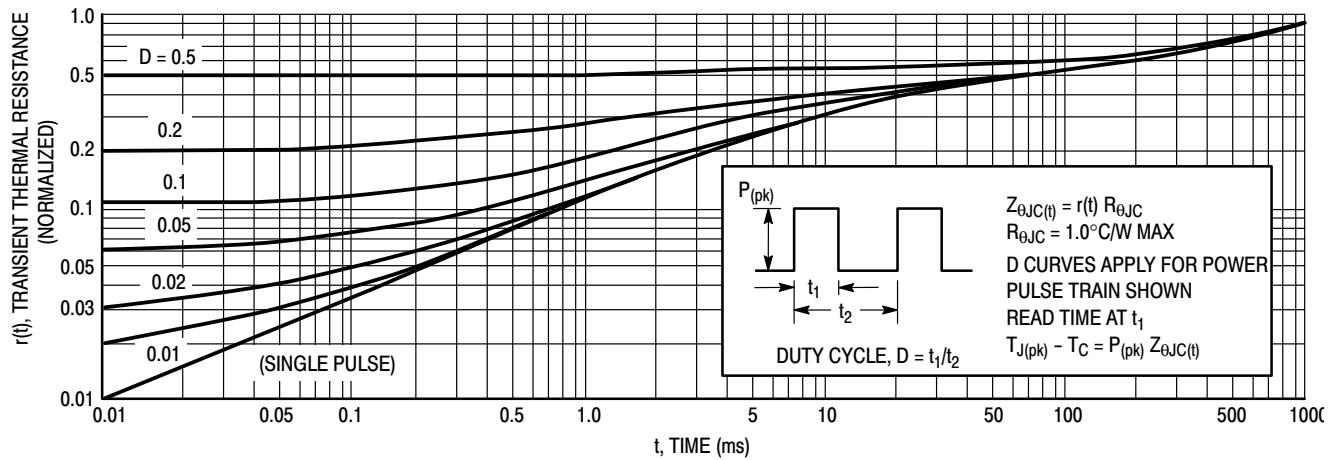


Figure 7. Thermal Response

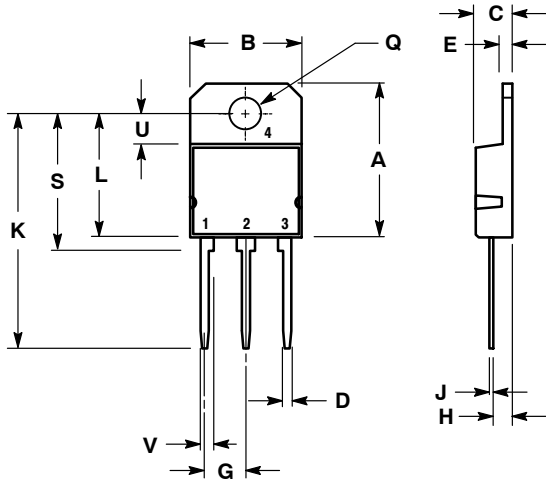
# BDV65B (NPN), BDV64B (PNP)

## PACKAGE DIMENSIONS

SOT-93 (TO-218)

CASE 340D-02

ISSUE E



NOTES:

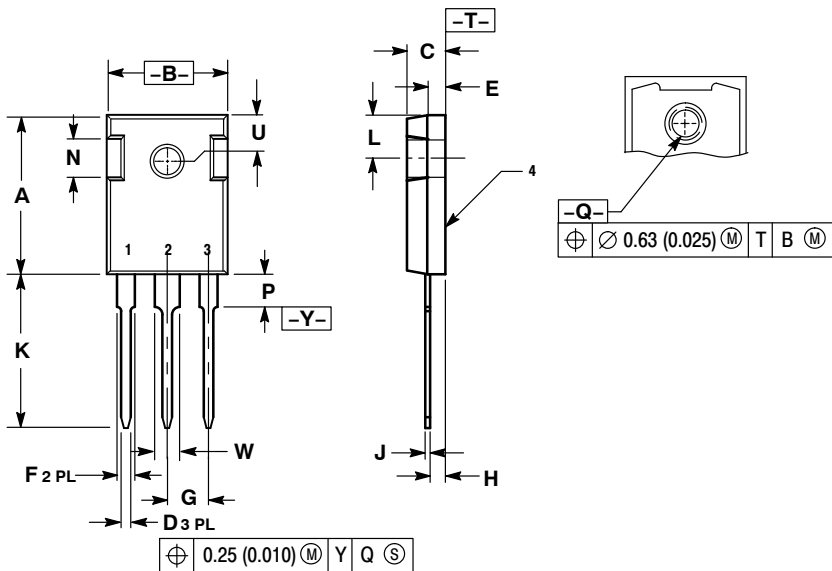
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

STYLE 1:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

TO-247  
CASE 340L-02  
ISSUE F



NOTES:


1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	---	4.50	---	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

STYLE 3:

- PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

# BDV65B (NPN), BDV64B (PNP)

**ON Semiconductor** and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
P.O. Box 5163, Denver, Colorado 80217 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкуренспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: [org@lifeelectronics.ru](mailto:org@lifeelectronics.ru)